TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC4W66F, TC4W66FU

DUAL BILATERAL SWITCH

The TC4W66 contains two independence circuits of bidirectional switches.

When control input CONT is set to "H" level, the impedance between input and output of the switch becomes low and when it is set to "L" level, the switch becomes high. This can be applied for switching of analog signals and digital signals.

FEATURES

• ON-resistance, RON

• OFF-resistance, ROFF

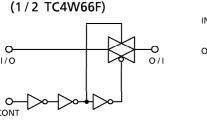
 R_{OFF} (Typ.) > $10^{9}\Omega$

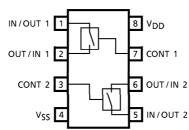
MAXIMUM RATINGS

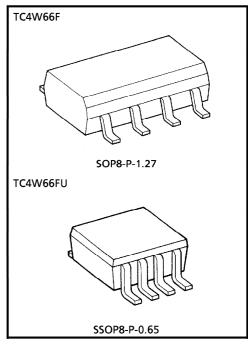
LOGIC DIAGRAM

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	Vss - 0.5~Vss + 20	V
Control Input Voltage	V _{C IN}	$V_{SS} = 0.5 \sim V_{DD} + 0.5$	٧
Switch I/O Voltage	V _{I/O}	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	٧
Power Dissipation	PD	300	mW
Potential difference across I/O during ON	V _I -V _O	± 0.5	٧
Control Input Current	IC IN	± 10	mA
Operating Temperature Range	T _{opr}	- 40~85	°C
Storage Temperature	T _{stg}	- 65∼150	°C
Lead Temp./Time	TL	260°C / 10s	

PIN ASSIGNMENT (TOP VIEW)

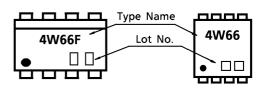






Weight SOP8-P-1.27 : 0.05g (Typ.) SSOP8-P-0.65 : 0.02g (Typ.)

MARKING



TRUTH TABLE

CONTROL	IMPEDANCE BETWEEN IN/OUT-OUT/IN *
Н	$0.5 \sim 5 \times 10^{2} \Omega$
L	>10 ⁹ Ω

* See static electrical characteristics.

RECOMMENDED OPERATING CONDITIONS ($V_{SS} = 0V$)

CHARACTERISTICS	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V _{DD}	_	3		18	V
Input/Output Voltage	V _{DD} /V _{OUT}		0		V_{DD}	V

CHARACTERISTICS	SYM- TEST		V_{DD}	Ta = -40°C		Ta = 25°C			Ta = 85°C		UNIT
CHARACTERISTICS	BOL	CONDITION	(V)	MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	OINIT
Control Input			5	3.5	_	3.5	2.75	_	3.5	_	
High Voltage	V _{IH}	$ I_{IS} = 10 \mu A$	10	7.0	—	7.0	5.50	_	7.0	—	
Ingh voltage			15	11.0	_	11.0	8.25		11.0	_	_v
Control Input			5	_	1.5	_	2.25	1.5		1.5	
Low Voltage	V _{IL}	$ I_{IS} = 10 \mu A$	10	_	3.0	_	4.5	3.0	_	3.0	
Low Voltage			15		4.0		6.75	4.0	_	4.0	
		$0 \le V_{IS} \le V_{DD}$	5	_	800	_	290	950	_	1200	
On-State Resistance	RON	$ R_L = 10k\Omega$	10	_	210	_	120	250	—	300	
			15		140	_	85	160	_	200	Ω
∆ On-State			5		_	_	10	_	_	_	32
Resistance (Between	RON 4	_	10	_	_	_	6	_	_	—	
Any2 Switches)			15	1	—	_	4			_	
		V _{IN} = 18V,	18		± 100		± 0.1	± 100		± 1000	
Input / Output Leakage Current IOFF		V _{OUT} = 0V	'0	_	- 100	_	- 0.	± 100		1000	nA
	OFF	$V_{IN} = 0V$,	18		± 100		± 0.1	± 100		± 1000	
		V _{OUT} = 18V									
Quiescent Device	ujescent Device	$V_{IN} = V_{DD}$	5	_	0.25	_	0.001	0.25	_	7.5	
Current	1 100		10	_	0.5	_	0.001	0.5	_	15	
		V _{SS} *	15		1.0	_	0.002	1.0	_	30	
Input H Level	ΊΗ	V _{IH} = 18V	18	_	0.1	_	10 ⁻⁵			1.0	
Current L Level	l _{IL}	V _{IL} = 0V	18	_	- 0.1	_	– 10 ^{– 5}	- 0.1	_	- 1.0	

DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, $V_{SS} = 0V$, $C_L = 50pF$)

CHARACTERISTICS	SYMBOL	TEST CONDITION	V _{SS} (V)	V _{DD} (V)	MIN.	TYP.	MAX.	UNIT
Phase Difference between Input to	φ Ι- Ο	C _L = 50pF	0 0	5 10		15 8	40 20	
Output			0	15	_	5	15	
Propagation Delay	+	$R_{L} = 1k\Omega$	0	5	_	55	120	
Time (CONTROL-OUT)	t _{pZL}	$C_L = 50pF$	0	10	_	25	40	ns
Time (continue out)	t _{pZH}	CL = 30pi	0	15	_	20	30	
Propagation Delay	t _{pLZ}	$R_{I} = 1k\Omega$	0	5	_	45	80	
Time (CONTROL-OUT)	t _{pHZ}	$C_L = 50pF$	0	10	_	30	70	
Time (continol oot)	чрни	CL = 30pi	0	15	_	25	60	
MAX. Control Input	f _{MAX}	$R_{I} = 1k\Omega$	0	5	_	10	—	
Repetition Rate	(C)	$C_L = 50pF$	0	10	_	12	—	
Repetition Rate	(C)	_	0	15	_	12		MHz
-3dB Cutoff	fMAX	$R_L = 1k\Omega$	_ 5	5		30		
Frequency	(I-O)	$C_L = 50pF$ (*1)				30		
Total Harmonic Distortion	_	$R_L = 10k\Omega$ $f = 1kHz \qquad (*2)$	- 5	5	_	0.03	_	%
– 50dB Feed through Frequency	_	$R_{L} = 1k\Omega \qquad (*3)$	- 5	5	1	600	1	kHz
– 50dB Crosstalk Frequency	_	$R_{L} = 1k\Omega \qquad (*4)$	- 5	5		1		MHz
Crosstalk (CONTROL-OUT)	_	$R_{IN} = 1k\Omega$	0	5	_	200	_	
		$R_{OUT} = 10k\Omega$	0	10	_	400	—	mV
		C _L = 15pF	0	15	_	600	_	
Input Capacitance	C _{IN}	Control Input				5	7.5	
input Capacitance		Switch I/O			_	10		nE
Feed through Capacitance	C _{IN-OUT}	_			_	0.5	_	pF

^{*1} Since wave of $\pm 2.5 V_{p-p}$ shall be used for V_{IS} and the frequency of $20 log_{10}$ $\frac{V_{OS}}{V_{IS}}$

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^{= -3}dB shall be f_{MAX}.

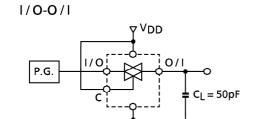
*2 V_{IS} shall be sine wave of ±2.5V_{p-p}.

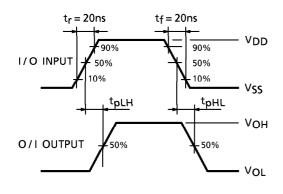
*3 Sine wave of ±2.5V_{p-p} shall be used for V_{IS} and the frequency of 20ℓog₁₀

= -50dB shall be feed-through.

^{*4} Sine wave of $\pm 2.5V_{p-p}$ shall be used for V_{IS} and the frequency of $20log_{10}$ $\frac{V_{OUT}}{V_{IS}}$ = -50dB shall be crosstalk.

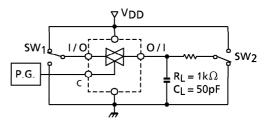
1. t_{pLH}, t_{pHL}

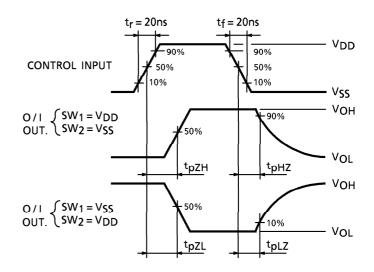




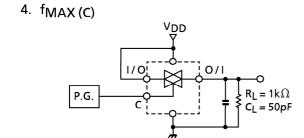
3. RON V_{DD} V_{IN} $V_{$

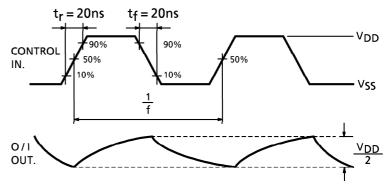
2. t_{pZL}, t_{pZH}, t_{pLZ}, t_{pHZ}
CONTROL-O/I



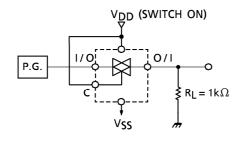


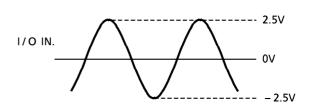
 $R_{\mbox{ON}} = 10 \times \ \frac{(\mbox{V}_{\mbox{IN}} - \mbox{V}_{\mbox{OUT}})}{\mbox{V}_{\mbox{OUT}}} (\mbox{k}\Omega)$

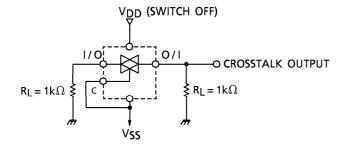




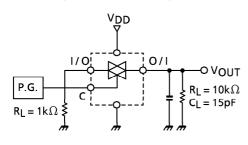
5. CROSSTALK (SWITCH I/O)

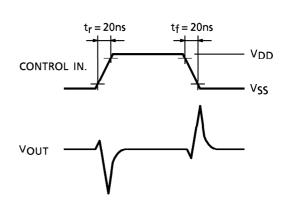




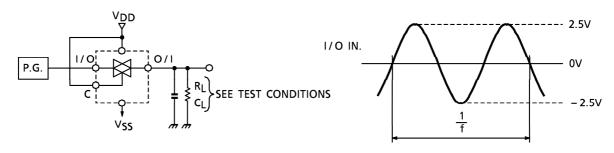


6. CROSSTALK (CONTROL INPUT)





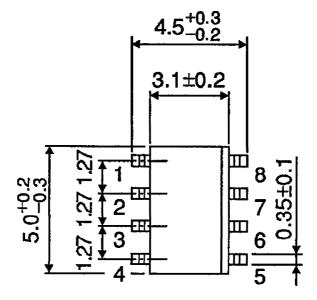
7. TOTAL HARMONIC DISTORTION, f_{MAX} (I/O-O/I), FEEDTHROUGH (SWITCH OFF)

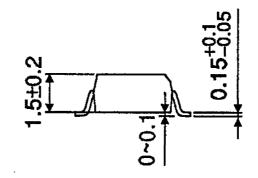


PACKAGE DIMENSIONS

SOP8-P-1.27

Unit: mm

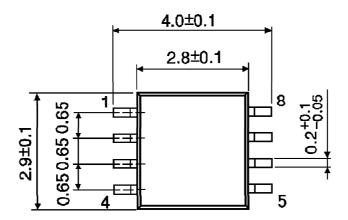


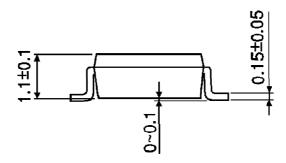


Weight: 0.05g (Typ.)

PACKAGE DIMENSIONS SSOP8-P-0.65

Unit : mm





Weight: 0.02g (Typ.)

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